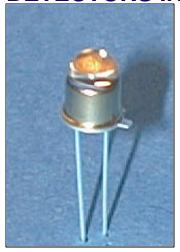
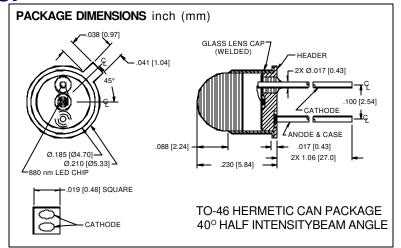
# **PHOTONIC** DETECTORS INC.

## **High-Power & Current GaAIAs Infrared Emitters** Peak Wavelength, 880 nm, Type PDI-E812





#### **FEATURES**

- Dual cathode
- High current
- · Medium emission angle

### **DESCRIPTION:** The **PDI-E812** infrared emitting **APPLICATIONS**

diode uses dual cathode, high current liquid phase epitaxially grown GaAlAs. Optimized for high power, high current at 880 nm. Packaged in

a TO-46 header with a glass lens cap.

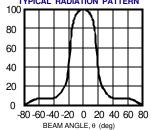
ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

				- /	_
SYMBOL	PARAMETER	MIN	MAX	UNITS	(%)
Pd	Power Dissipation		360	mW	
l <sub>EP</sub>	Continuous Forward Current		180	mA	į
 Ep	Peak Forward Current (100µs pulse,10pps	)	3.0	Α	MH.
V <sub>R</sub>	Reverse voltage		3.0	V	P
To & Ts	Storage & Operating Temperature	-65	+125	°C	] }
TS	Soldering Temperature*		+260	°C	ZFI A
*1/16 inch from cas	a for 3 care may				

\*1/16 inch from case for 3 secs max

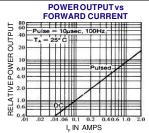
- Photoelectric switches
  - Reflective switches
- Smoke detectors

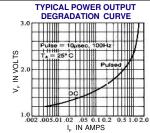
TYPICAL RADIATION PATTERN

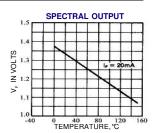


#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Po	Output Power	I <sub>F</sub> = 100 mA	7.0	15		mW
VF	Forward Voltage	I= 100 mA		1.5	1.9	V
IR	Reverse Current	V <sub>R</sub> = -3.0 V			10	mA
λp	Peak Wavelength	I <sub>F</sub> = 50 mA	865	880	895	nm
Dλ	Spectral Halfwidth	I <sub>F</sub> = 50 mA		80		nm
Rd	Dynamic Resistance	I <sub>=</sub> = 100 mA		1.2		Ohm
tr	Rise Time	l <sub>F</sub> = 100 mA		0.6		μS
<b>t</b> f	Fall Time	l⊧ = 100 mA		0.5		<b>m</b> S







Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. Optical power and radiant intensity measured using uncapped dimpled TO-46 into integrating sphere.